



### **40V P-Channel Enhancement Mode MOSFET**

Voltage

-40 V

Current

-45 A

#### **Features**

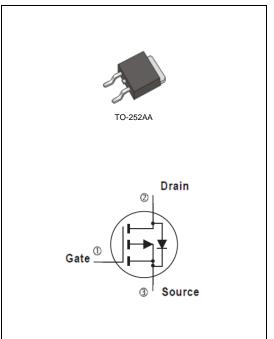
- $R_{DS(ON)}$ ,  $V_{GS}$ @-10V,  $I_{D}$ @-15A<17m $\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@-4.5V$ ,  $I_D@-10A<25m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 Standard

#### **Mechanical Data**

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	-40		
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T <sub>C</sub> =25°C	l <sub>D</sub>	-45		
	T <sub>C</sub> =100°C		-28	Α	
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	-135	i	
Power Dissipation	T <sub>C</sub> =25°C	Po	63	W	
	T <sub>C</sub> =100°C		25	VV	
Continuous Drain Current (Note 4)	T <sub>A</sub> =25°C	I <sub>D</sub>	-8.5	_	
	T <sub>A</sub> =70°C		-7	Α	
Power Dissipation	T <sub>A</sub> =25°C	Ĺ.	2.0	W	
	T <sub>A</sub> =70°C	Pb	1.3		
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	2.0	°C/W	
	Junction to Ambient	$R_{\theta,JA}$	62.5		

• Limited only By Maximum Junction Temperature





### **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-40	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-1	-1.6	-2.5		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A	_	14	17	mΩ	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	-	20	25		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V	-	-	-1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	$Q_g$	V <sub>DS</sub> =-32V, I <sub>D</sub> =-10A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	19	-	nC	
Gate-Source Charge	$Q_gs$		-	5.3	-		
Gate-Drain Charge	$Q_gd$		-	6.6	-		
Input Capacitance	Ciss	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1MHZ	-	2030	-	pF	
Output Capacitance	Coss		-	190	-		
Reverse Transfer Capacitance	Crss	I=IIVIIIZ	-	139	-		
Turn-On Delay Time	td <sub>(on)</sub>	\/ 00\/ I 4A	-	8.6	-		
Turn-On Rise Time	t <sub>r</sub>	$V_{DS}$ =-20V, $I_{D}$ =-1A, $V_{GS}$ =-10V, $R_{G}$ =6 $\Omega$ (Note 1.2)	-	9.6	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>		-	77	-		
Turn-Off Fall Time	t <sub>f</sub>		-	39	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	,		-	-	-45	А	
Diode Forward Current	I <sub>S</sub>						
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V	-	-0.71	-1	V	

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$  =25°C.
- 4. The maximum current rating is package limited.
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

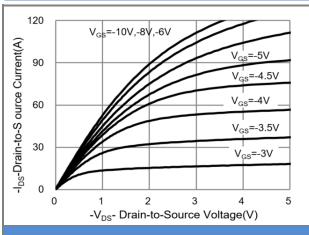


Fig.1 On-Region Characteristics

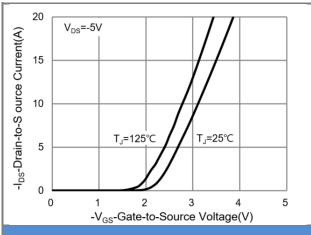


Fig.2 Transfer Characteristics

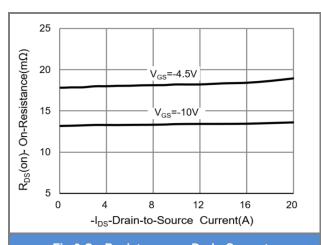


Fig.3 On-Resistance vs. Drain Current

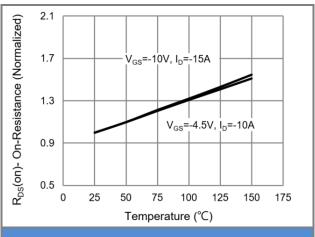


Fig.4 On-Resistance vs. Junction temperature

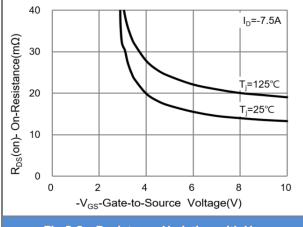


Fig.5 On-Resistance Variation with V<sub>GS</sub>

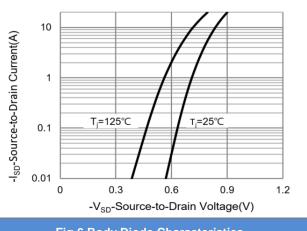


Fig.6 Body Diode Characteristics





#### TYPICAL CHARACTERISTIC CURVES

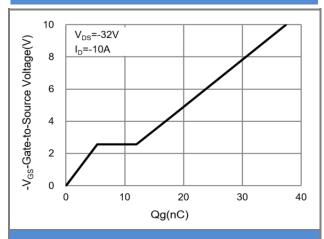


Fig.7 Gate-Charge Characteristics

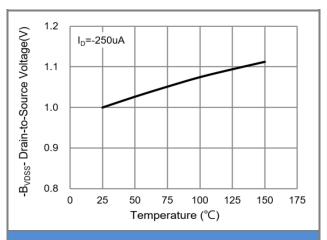


Fig.8 Breakdown Voltage Variation vs. Temperature

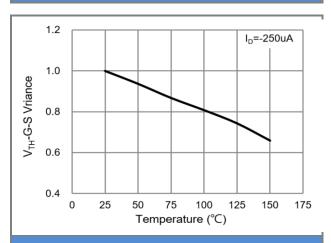


Fig.9 Threshold Voltage Variation with Temperature

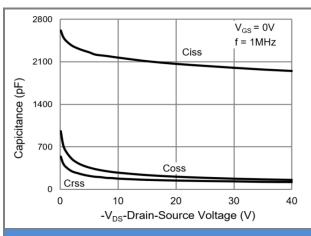
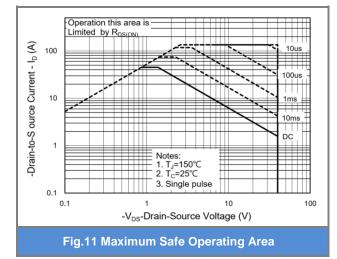


Fig.10 Capacitance vs. Drain-Source Voltage



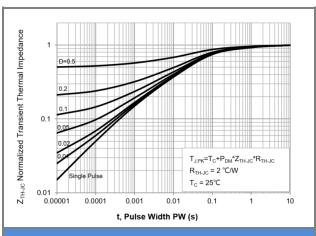


Fig.12 Normalized Thermal Transient Impedance

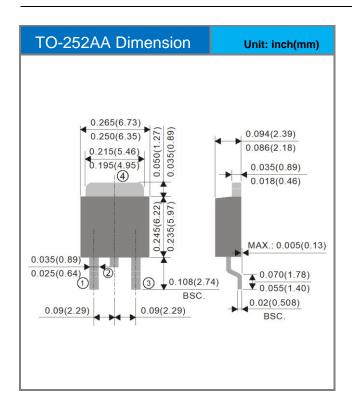


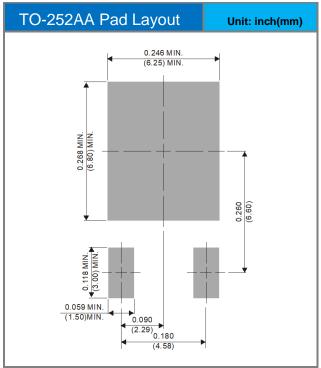


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJD45P04-AU_L2_000A1	TO-252AA	3,000pcs / 13" reel	D45P04	Halogen free	

### **Packaging Information & Mounting Pad Layout**









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